

Abstract

A bidirectional semiconductor component has two symmetrical MOS transistor structures integrated laterally in a substrate and connected antiseriably, their drain terminals being
5 connected to one another.

A zone (28) having the same type of conductivity as the drain region yet a higher doping than that of the drain region (12) is situated upstream from a pn junction (22) of one of the MOS transistors (26) in a junction area with the drain region (12).

(Figure 1)